



P-Channel 2.5-V (G-S) MOSFET

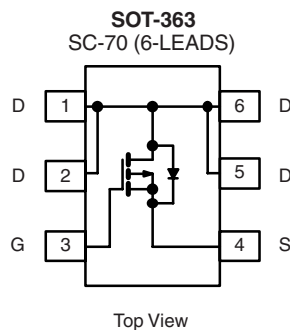
PRODUCT SUMMARY			
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A)	Q _g (Typ)
- 20	0.150 at V _{GS} = - 4.5 V	- 1.5	2.9
	0.175 at V _{GS} = - 3.6 V	- 1.4	
	0.265 at V _{GS} = - 2.5 V	- 1.2	

FEATURES

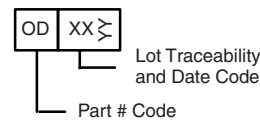
- TrenchFET[®] Power MOSFET



RoHS
COMPLIANT



Marking Code



Ordering Information: Si1403BDL-T1-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage	V _{DS}	- 20		V	
Gate-Source Voltage	V _{GS}	± 12			
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	- 1.5	- 1.4	A
		T _A = 85 °C	- 1.2	- 1.0	
Pulsed Drain Current	I _{DM}	- 5			
Continuous Diode Current (Diode Conduction) ^a	I _S	- 0.8	- 0.8		
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	0.625	0.568	W
		T _A = 85 °C	0.400	0.295	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R _{thJA}	t ≤ 5 s	165	200	°C/W
		Steady State	180	220	
Maximum Junction-to-Foot (Drain)	R _{thJF}	105	130		

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.



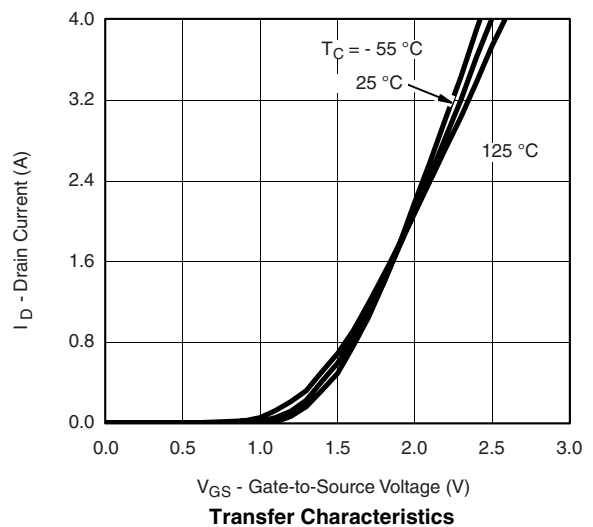
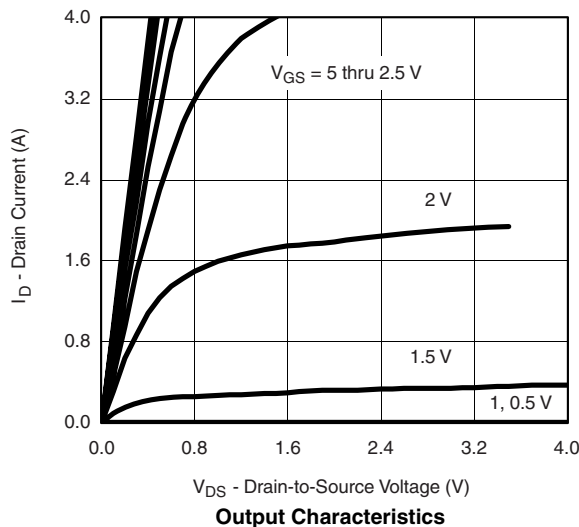
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.6		-1.3	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$			-5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -4.5\text{ V}$	-2			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -1.5\text{ A}$		0.120	0.150	Ω
		$V_{GS} = -3.6\text{ V}, I_D = -1.4\text{ A}$		0.140	0.175	
		$V_{GS} = -2.5\text{ V}, I_D = -0.8\text{ A}$		0.220	0.265	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\text{ V}, I_D = -1.5\text{ A}$		3.4		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -0.8\text{ A}, V_{GS} = 0\text{ V}$		-0.8	-1.1	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -1.5\text{ A}$		29	4.5	nC
Gate-Source Charge	Q_{gs}		0.65			
Gate-Drain Charge	Q_{gd}		1.0			
Gate Resistance	R_g	$f = 1.0\text{ MHz}$		9		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 6\text{ }\Omega$		13	20	ns
Rise Time	t_r		30	45		
Turn-Off Delay Time	$t_{d(off)}$		28	42		
Fall Time	t_f		13	20		
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -0.8\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		12	25	
Body Diode Reverse Recovery Charge	Q_{rr}			4	8	nC

Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

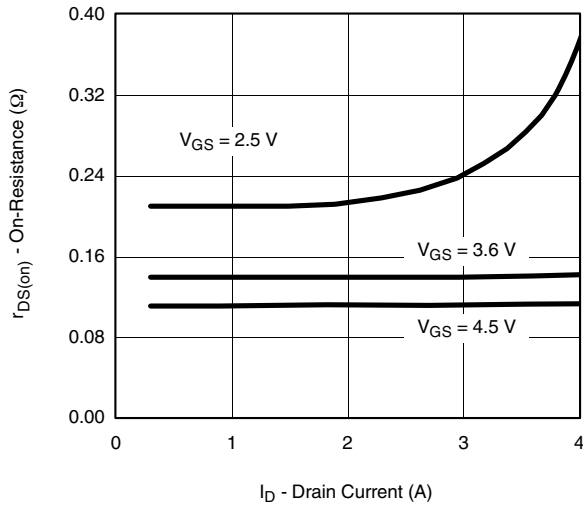
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted

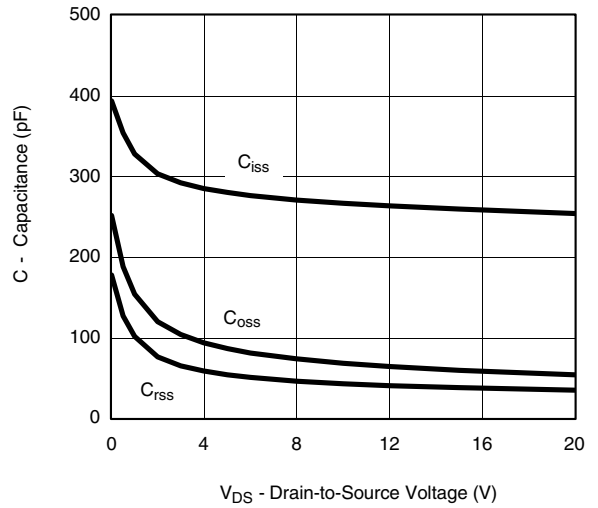




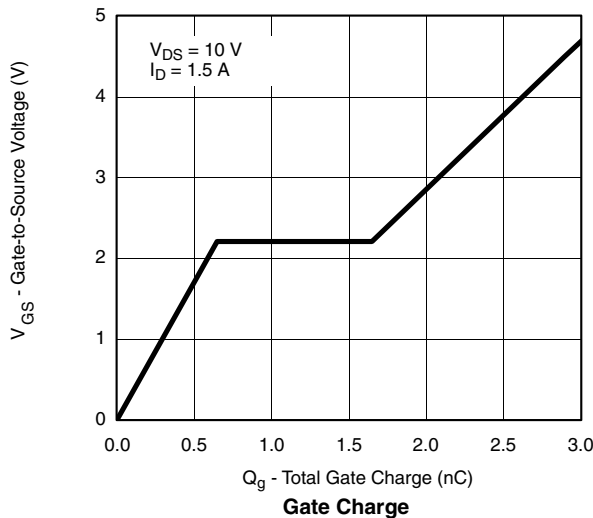
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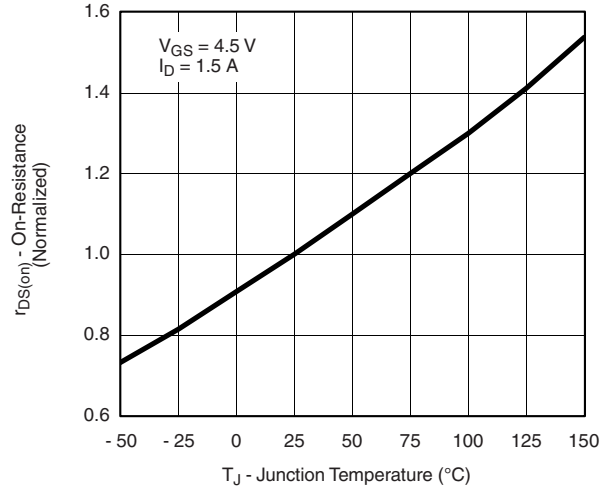
On-Resistance vs. Drain Current



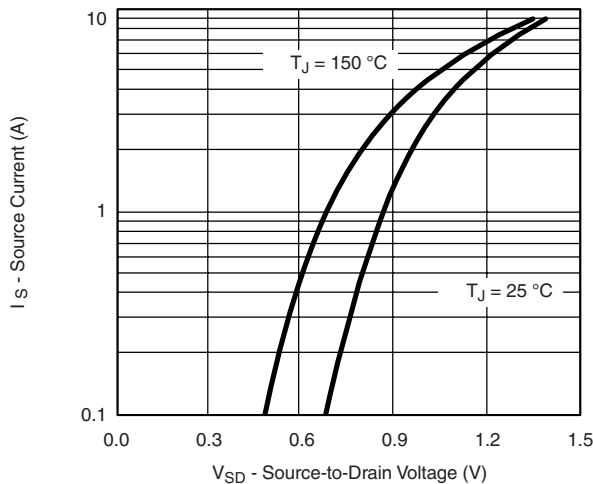
Capacitance



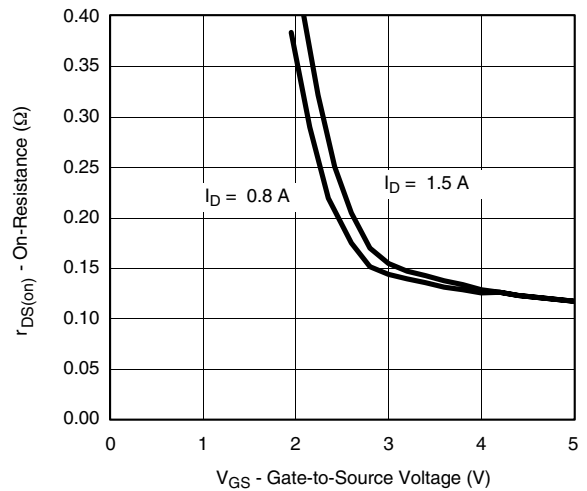
Gate Charge



On-Resistance vs. Junction Temperature



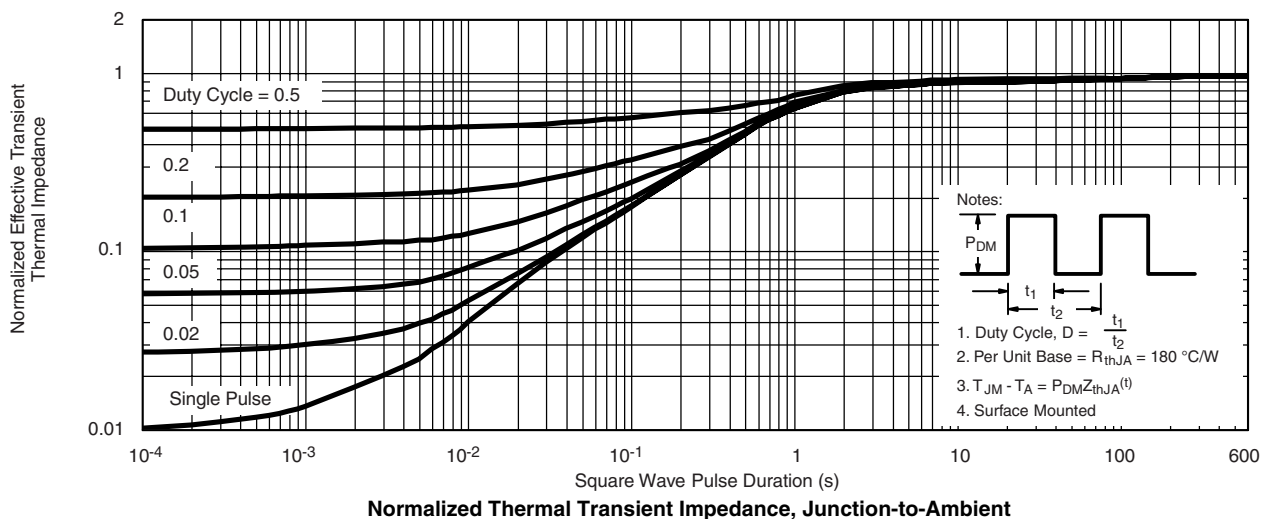
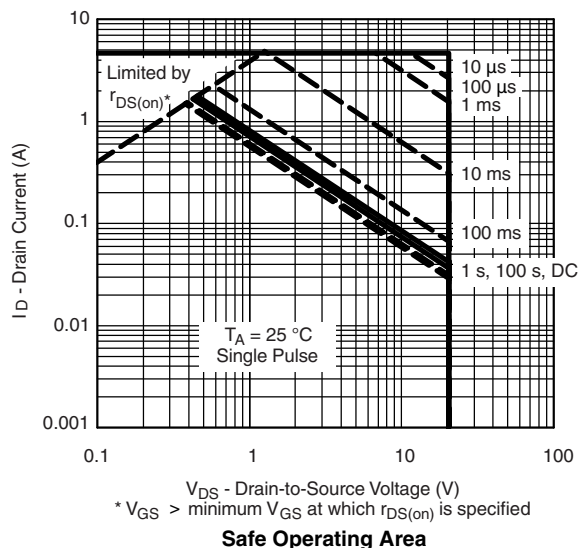
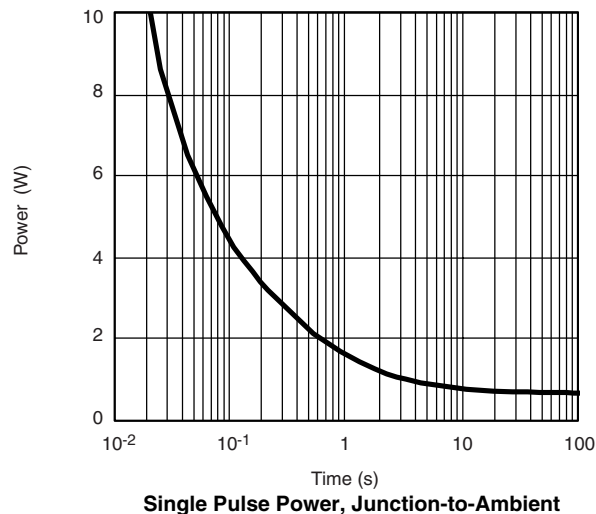
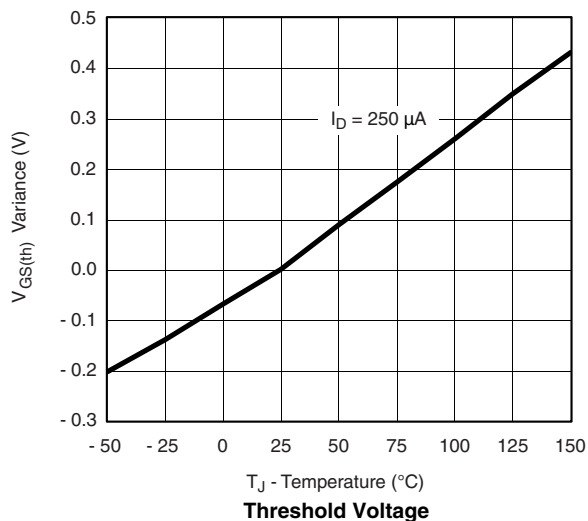
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

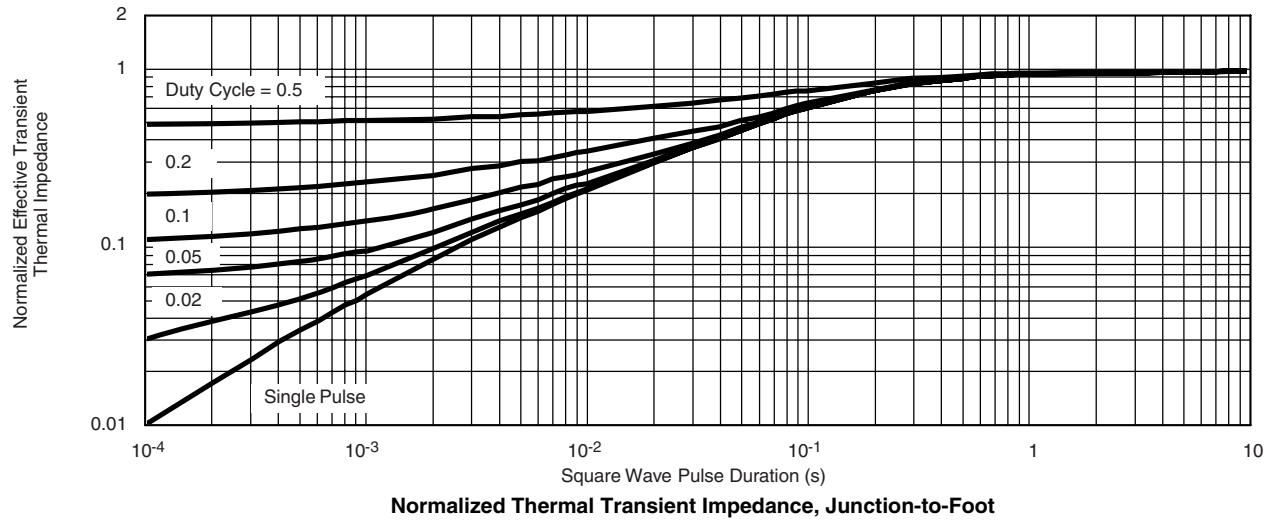


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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